GMBTA64

PNP SILICON TRANSISTOR

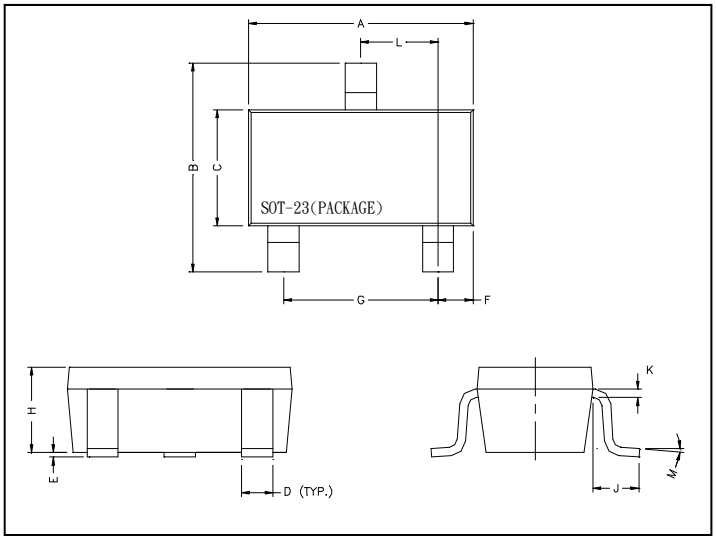
Description

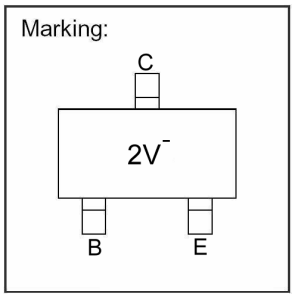
The GMBTA64 is designed for application requiring extremely high current gain at collector current to 500mA.

Features

- High D.C. Current Gain
- For Complementary with NPN Type GMBTA14

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25℃

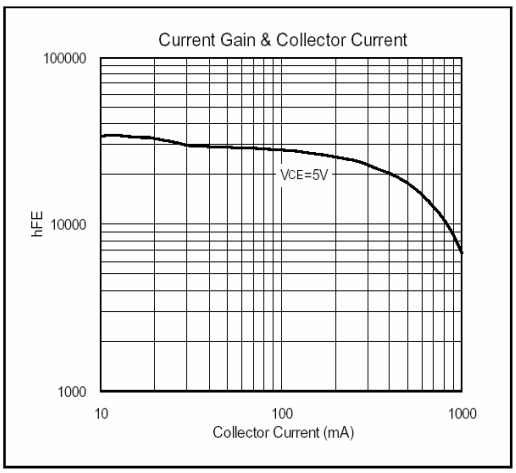
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-10	V
Collector Current	I_C	-500	mA
Total Power Dissipation	P_D	225	mW

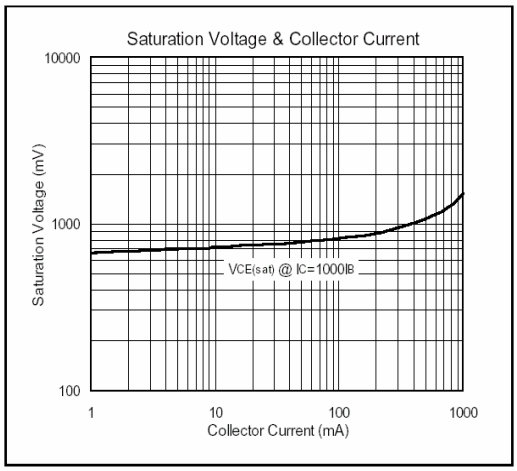
Characteristics at Ta = 25℃

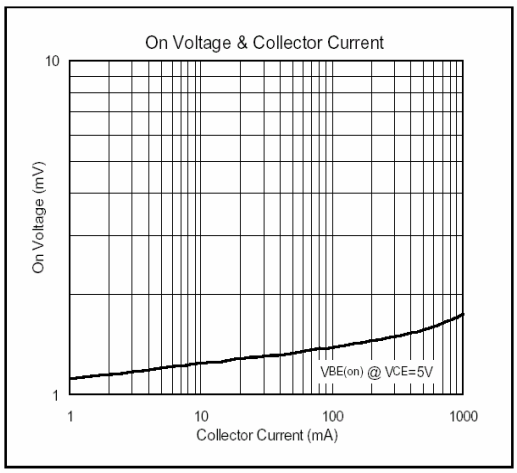
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-30	-	-	V	I_C=-100uA , I_E=0
BV_{CES}	-30	-	-	V	I_C=-100uA, I_B=0
BV_{EBO}	-10	-	-	V	I_E=-10uA, I_C=0
I_{CBO}	-	-	-100	nA	V_{CB}=-30V, I_E=0
I_{EBO}	-	-	-100	nA	V_{CE}=-10V
V_{CE}(sat)	-	-	-1.5	V	I_C=-100mA, I_B=-0.1mA
V_{BE}(on)	-	-	-2	V	V_{CE}=-5V, I_C=-100mA
HFE1	10K	-	-		V_{CE}=-5V, I_C=-10mA
HFE2	20K				V_{CE}=-5V, I_C=-100mA
fT	125	-	-	MHz	V_{CE}=-5V, I_C=-100mA, f=100MHz

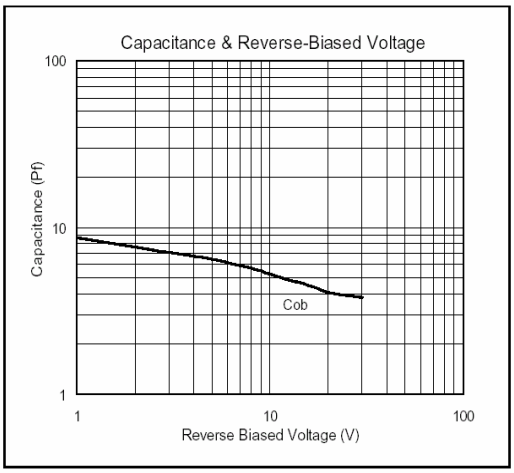
*Pulse Test :Pulse width ≤380us,Duty Cycly≤2%

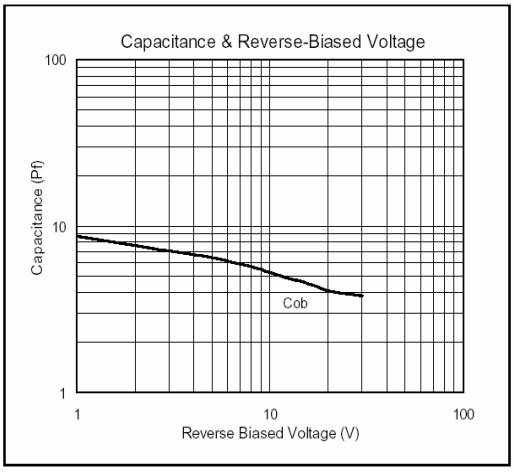
Characteristics Curve

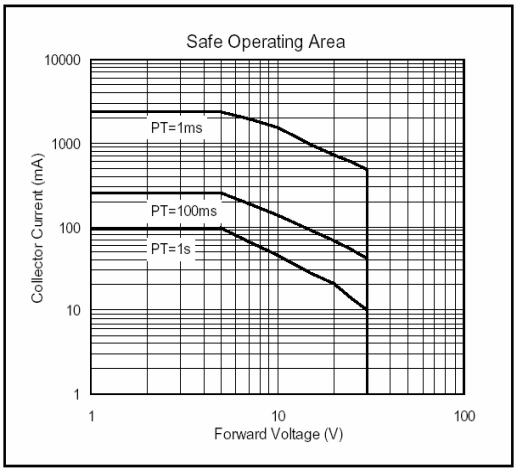












Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165